



N-Channel 60 V (D-S), 175 °C MOSFET, Logic Level

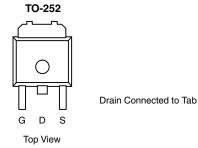
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a		
60	0.0093 at V _{GS} = 10 V	50		
00	$0.0122 \text{ at V}_{GS} = 4.5 \text{ V}$	50		

FEATURES

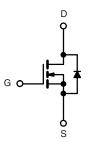
- 175 °C Junction Temperature
- TrenchFET® Power MOSFET

Material categorization: For definitions of compliance please see www.vishay.com/doc?99912





Ordering Information: SUD50N06-09L-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current /T 175 °C\b	T _C = 25 °C	L	50			
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 100 °C	- I _D	50 ^a			
Pulsed Drain Current	I _{DM}	100	A			
Continuous Source Current (Diode Conduction)	I _S	50 ^a	1			
Avalanche Current	I _{AS}	50	1			
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	125	mJ		
Maximum Power Dissipation	T _C = 25 °C	P _D	136	w		
Maximum Fower Dissipation	T _A = 25 °C	' D	3 ^b , 8.3 ^{b, c}	VV		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marrian III I Ambient	t ≤ 10 sec	В	15	18		
Maximum Junction-to-Ambient ^a	Steady State	- R _{thJA}	40	50	°C/W	
Maximum Junction-to-Case	·	R _{thJC}	0.85	1.1		

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $c.\ t \leq 10\ s.$

SUD50N06-09L

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SPECIFICATIONS $(T_J = 25)$	°C, unless o	otherwise noted)					
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static	•		•	•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	2	3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 60 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			Α	
		V _{GS} = 10 V, I _D = 20 A		0.0074	0.0093		
5 . 6 . 6 5 h	В	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.0160		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C			0.0200	Ω	
		V _{GS} = 4.5 V, I _D = 15 A			0.0122		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S	
Dynamic	•		•	•			
Input Capacitance	C _{iss}			2650			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		470		pF	
Reverse Transfer Capacitance	C _{rss}			225			
Total Gate Charge ^c	Q_g			47	70		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10		nC	
Gate-Drain Charge ^c	Q_{gd}			12			
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, R_L = 0.6 \Omega$ $I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		15	25		
Turn-Off Delay Time ^c	t _{d(off)}			35	50	ns	
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)			<u> </u>		
Pulsed Current	I _{SM}				100	Α	
Diode Forward Voltage	V_{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		45	100	ns	

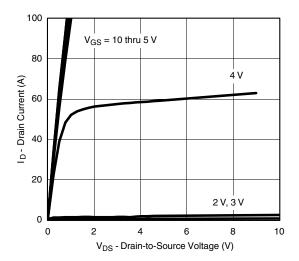
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. Independent of operating temperature.

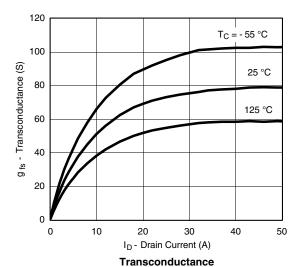
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C unless noted)



Output Characteristics



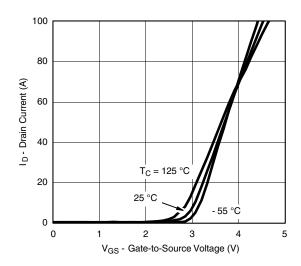
3000 C_{iss} C - Capacitance (pF) 2500 2000 1500 1000 C_{oss} 500 $\mathsf{C}_{\mathsf{rss}}$ 0

V_{DS} - Drain-to-Source Voltage (V) Capacitance

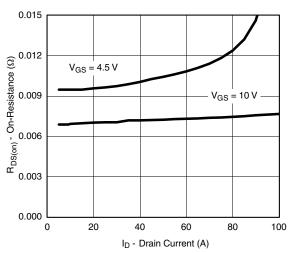
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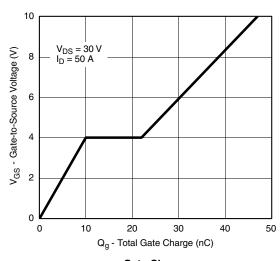
60



Transfer Characteristics



On-Resistance vs. Drain Current



10

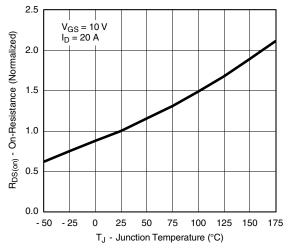
0

4000 3500

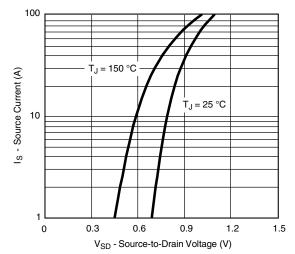
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TYPICAL CHARACTERISTICS (25 °C unless noted)



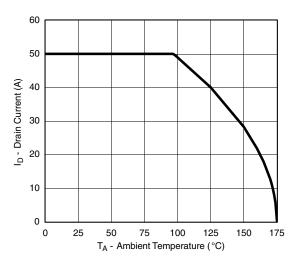
On-Resistance vs. Junction Temperature

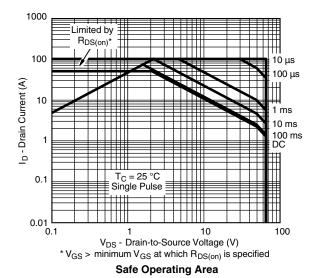


Source-Drain Diode Forward Voltage

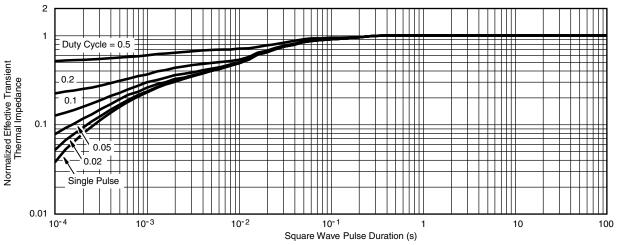


THERMAL RATINGS





Maximum Drain Current vs. Ambient Temperature



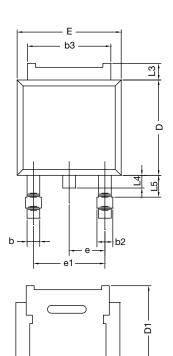
Normalized Thermal Transient Impedance, Junction-to-Case

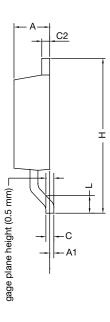
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TO-252AA Case Outline





	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC		0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T16-0236-Rev. P, 16-May-16					

DWG: 5347

Notes

• Dimension L3 is for reference only.

Revision: 16-May-16 Document Number: 71197



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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ATTLICATION NOT



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